



# Faculty of Engineering

## End Semester Examination May 2025

### EC3CO03 Electronic Devices & Circuits

<b>Programme</b>	<b>:</b>	<b>B.Tech.</b>	<b>Branch/Specialisation</b>	<b>:</b>	<b>EC</b>
<b>Duration</b>	<b>:</b>	<b>3 hours</b>	<b>Maximum Marks</b>	<b>:</b>	<b>60</b>

**Note:** All questions are compulsory. Internal choices, if any, are indicated. Assume suitable data if necessary. Notations and symbols have their usual meaning.

Section 1 (Answer all question(s))					Marks	CO	BL
<b>Q1.</b>	The diffused impurities with _____ valence electrons are called donor atoms.				1	1	1
	<input type="radio"/> 4	<input type="radio"/> 3					
	<input checked="" type="radio"/> 5	<input type="radio"/> 2					
<b>Q2.</b>	Schottky diodes are also known as-				1	1	1
	<input type="radio"/> PIN diodes	<input checked="" type="radio"/> Hot carrier diodes					
	<input type="radio"/> Step-recovery diodes	<input type="radio"/> Tunnel diodes.					
<b>Q3.</b>	A transistor has a $\beta_{DC}$ of 250 and a base current, $I_B$ , of $20\mu A$ . The collector current, $I_C$ , equals:				1	2	1
	<input type="radio"/> $500\mu A$	<input checked="" type="radio"/> 5 mA					
	<input type="radio"/> 50mA	<input type="radio"/> 5A					
<b>Q4.</b>	When transistors are used in digital circuits they usually operate in the:				1	2	1
	<input type="radio"/> Active region	<input type="radio"/> Breakdown region					
	<input checked="" type="radio"/> Saturation and cut off regions	<input type="radio"/> Linear region					
<b>Q5.</b>	A JFET is also called _____ transistor.				1	3	1
	<input checked="" type="radio"/> Unipolar	<input type="radio"/> Bipolar					
	<input type="radio"/> Unijunction	<input type="radio"/> None of the above					
<b>Q6.</b>	With the E-MOSFET, when gate input voltage is zero, drain current is:				1	3	1
	<input type="radio"/> At saturation	<input checked="" type="radio"/> Zero					
	<input type="radio"/> $I_{DSS}$	<input type="radio"/> Widening the channel					
<b>Q7.</b>	What should be the value of input resistance for an ideal voltage amplifier circuit?				1	4	1
	<input type="radio"/> Zero	<input type="radio"/> Unity					
	<input checked="" type="radio"/> Infinity	<input type="radio"/> Unpredictable					
<b>Q8.</b>	Why is RC coupling confined to low power applications?				1	4	1
	<input type="radio"/> Due to large value of coupling capacitor	<input checked="" type="radio"/> Low efficiency					
	<input type="radio"/> Large number of components	<input type="radio"/> Due to its frequency response					
<b>Q9.</b>	In an LC oscillator, the frequency of oscillator is _____ L or C.				1	5	1
	<input type="radio"/> Proportional to square of	<input type="radio"/> Directly proportional to					
	<input type="radio"/> Independent of the values of	<input checked="" type="radio"/> Inversely proportional to square root of					
<b>Q10.</b>	Only the condition $\beta A =$ _____ must be satisfied for self-sustained oscillations to result.				1	5	1
	<input checked="" type="radio"/> 1	<input type="radio"/> 0					
	<input type="radio"/> -1	<input type="radio"/> None of the above					

### Section 2 (Answer all question(s))

Marks CO BL

**Q11.** Define diffusion and drift current.

2 1 1

Rubric	Marks
Define diffusion current.	1
Define drift current.	1

**Q12.** Explain the Hall effect.

3 1 1

**Q13. (a)** Draw and explain the full wave center tapped rectifier circuit and also derive the expression for their efficiency.

5 2 1

Rubric	Marks
Draw and explain the full wave center tapped rectifier circuit.	2
For full wave center tapped rectifier circuit drive the expression for their efficiency.	3

(OR)

**(b)** Draw and explain the V I characteristic of Tunnel diode. Explain the tunnelling phenomenon.

Rubric	Marks
Draw the V I characteristic of Tunnel diode.	2
explain the V I characteristic of Tunnel diode.	3

### Section 3 (Answer all question(s))

Marks CO BL

**Q14.** Explain dc load line of transistor.

2 2 1

**Q15.** Derive relation between  $\alpha$ ,  $\beta$  and  $\gamma$  in transistor.

3 2 1

**Q16. (a)** Explain the input and output characteristics of transistor in CE configuration. Also explain the regions of operation.

5 2 1

(OR)

**(b)** Explain the h parameter model and find out input impedance, voltage gain and current gain in terms of h parameter.

### Section 4 (Answer all question(s))

Marks CO BL

**Q17.** What is pinch off condition?

2 3 1

**Q18.** Write down the difference between BJT and FET. (any3)

3 3 2

**Q19. (a)** Explain the working principal of n channel JFET with their characteristics.

5 3 1

Rubric	Marks
Explain the working principal of n channel JFET .	2
Characteristics of n channel JFET .	3

(OR)

**(b)** Explain the working principal of n channel enhancement type MOSFET with their characteristics.

Rubric	Marks
Draw construction diagram of n channel Enhancement type MOSFET.	2
Explain n channel Enhancement type MOSFET the working principal with their characteristics.	3

**Section 5 (Answer any 2 question(s))**

Marks CO BL

**Q20.** With the help of circuit diagram and waveform explain the operation of class B push pull power amplifier. Calculate its maximum power efficiency.

5 3 3

Rubric	Marks
Circuit diagram a of class B push pull power amplifier.	2
Draw waveform explain the operation of class B push pull power amplifier.	3

**Q21.** Explain the working of darlington pair amplifier. Why bootstrapping is done?

5 4 3

**Q22.** Draw and explain the working of RC coupled amplifier.

5 4 1

**Section 6 (Answer any 2 question(s))**

Marks CO BL

**Q23.** Explain various feedback topologies. Also derive an expression for input and output resistance for any one them.

5 4 3

**Q24.** Explain the working of Hartley oscillators. Also derive an expression for frequency of oscillation.

5 5 3

**Q25.** Explain the concept of feedback. Which feedback is generally used and why?

5 5 3

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